Shantou Huashan Electronic Devices Co.,Ltd.

NPN SILICON TRANSISTOR

HE13001

HIGH VOLTAGE SWITCH MODE APPLICICATIONS

High Speed Switching
Suitable for Switching Regulator and Montor Control

ABSOLUTE MAXIMUM RATINGS (T_a=25℃)

T_{stg}——Storage Temperature····· -55~150℃

T_j——Junction Temperature·····150℃

P_C——Collector Dissipation·····900mW

V_{CBO}——Collector-Base Voltage·····600V

V_{CEO}——Collector-Emitter Voltage·····400V

V_{EBO}——Emitter-Base Voltage·····9V

I_C——Collector Current·····0.25A

TO-92

1—Emitter，E
2—Collector，C
3—Base，B

ELECTRICAL CHARACTERISTICS (T_a=25℃)

Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
BV_{CBO}	Collector-Base Breakdown Voltage	600			V	I_C=1mA, I_E=0
BV_{CEO}	Collector-Emitter Breakdown Voltage	400			V	I_C=10mA, I_B=0
BV_{EBO}	Emitter-Base Breakdown Voltage	9			V	I_E=1mA， I_C=0
I_{CBO}	Collector Cut-off Current			100	μA	V_{CB}=500V, I_E=0
I_{EBO}	Emitter-Base Cut-off Current			100	μA	V_{EB}=9V, I_C=0
H_{FE}	DC Current Gain	8		70		V_{CE}=10V, I_C=20mA
$V_{CE(sat)}$	Collector- Emitter Saturation Voltage			0.6	V	I_C=100mA, I_B=20mA
$V_{BE(sat)}$	Base-Emitter Saturation Voltage			1.2	V	I_C=100mA, I_B=20mA
f_T	Current Gain-Bandwidth Product	8			MHz	V_{CE}=10V, I_C=20mA